

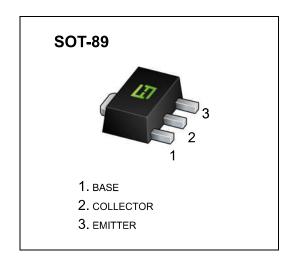
TRANSISTOR (NPN)

#### **FEATURES**

Power dissipation

### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	40	٧
V <sub>CEO</sub>	Collector-Emitter Voltage	30	٧
V <sub>EBO</sub>	Emitter-Base Voltage	6	٧
Ic	Collector Current -Continuous	3	Α
Pc	Collector Power Dissipation	0.5	W
R <sub>ΘJA</sub>	Thermal Resistance from Junction to Ambient	250	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~150	°C



Marking: .D882

#### ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

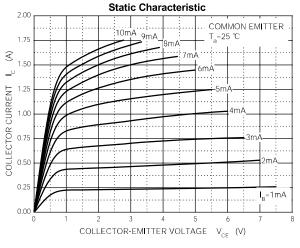
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	$I_{\rm C}$ = 10mA, $I_{\rm B}$ =0	30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V, I <sub>E</sub> =0			1	μΑ
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = 30V, I <sub>B</sub> =0			10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 6V, I <sub>C</sub> =0			1	μA
DC ourrent sain	h <sub>FE(1)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> = 1A	60		400	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> = 100mA	32			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 2A, I <sub>B</sub> = 0.2 A			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 2A, I <sub>B</sub> = 0.2 A			1.5	V
Transition frequency	f⊤	V <sub>CE</sub> = 5V , Ic=0.1A f =10MHz	50			MHz

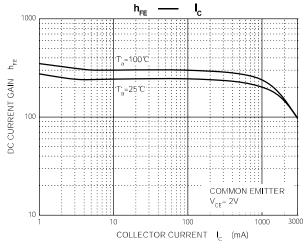
#### **CLASSIFICATION OF h**<sub>FE(1)</sub>

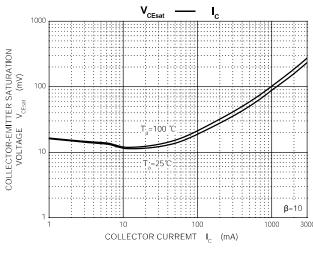
Rank	R	0	Y	GR
Range	60-120	100-200	160-320	200-400

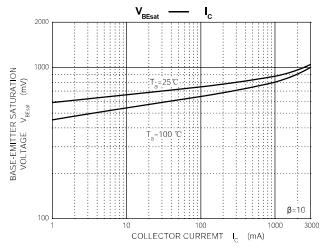
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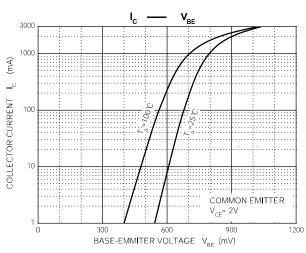


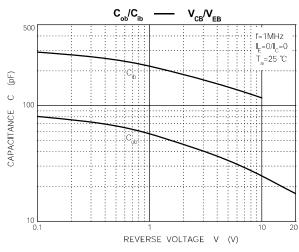


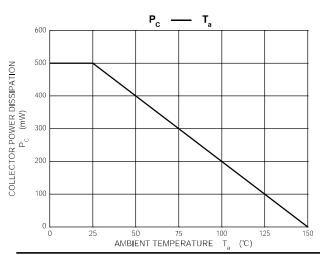






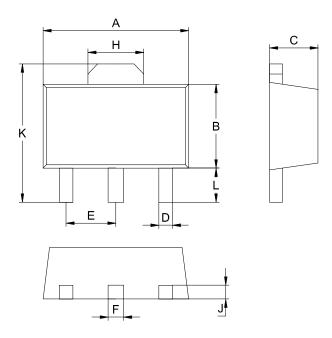






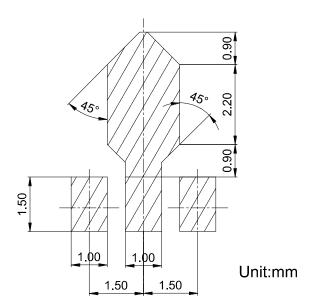
TRANSISTOR (NPN)

# **SOT-89 Package Outline Dimensions**



SOT-89				
Dim	Min	Max		
Α	4.30	4.70		
В	2.20	2.70		
С	1.30	1.70		
D	0.30	0.60		
E	1.40	1.60		
F	0.30	0.60		
Н	1.40	1.80		
J	0.30	0.60		
L	0.90	1.10		
K	3.75	4.35		
All Dimensions in mm				

## **SOT-89 Suggested Pad Layout**



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